MPS2222A is a Preferred Device

General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MPS2222 MPS2222A	V _{CEO}	30 40	Vdc
Collector-Base Voltage MPS2222 MPS2222A	V _{CBO}	60 75	Vdc
Emitter-Base Voltage MPS2222 MPS2222A	V _{EBO}	5.0 6.0	Vdc
Collector Current – Continuous	I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

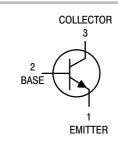
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

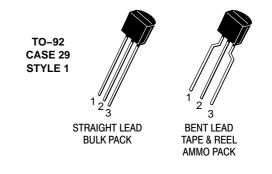
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com





MARKING DIAGRAMS





= Assembly Location

= Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	MPS2222 MPS2222A	V _{(BR)CEO}	30 40		Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	MPS2222 MPS2222A	$V_{(BR)CBO}$	60 75	_ _	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	MPS2222 MPS2222A	$V_{(BR)EBO}$	5.0 6.0	_ _	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MPS2222A	I _{CEX}	-	10	nAdc
Collector Cutoff Current	MPS2222 MPS2222A MPS2222 MPS2222A	I _{CBO}	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)	MPS2222A	I _{EBO}	-	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MPS2222A	I_{BL}	_	20	nAdc
ON CHARACTERISTICS			T		T
DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}, T_A=-55^{\circ}C) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \text{ (Note 1)} \\ (I_C=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \text{ (Note 1)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \text{ (Note 1)} \\ \end{array} $	MPS2222A only MPS2222 MPS2222A	h _{FE}	35 50 75 35 100 50 30 40	- - - 300 - -	_
Collector – Emitter Saturation Voltage (Note 1) $(I_{C} = 150 \text{ mAdc}, I_{B} = 15 \text{ mAdc})$ $(I_{C} = 500 \text{ mAdc}, I_{B} = 50 \text{ mAdc})$	MPS2222 MPS2222A MPS2222 MPS2222A	V _{CE(sat)}	- - -	0.4 0.3 1.6 1.0	Vdc
Base-Emitter Saturation Voltage (Note 1) $(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MPS2222 MPS2222A MPS2222 MPS2222A	V _{BE(sat)}	- 0.6 - -	1.3 1.2 2.6 2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Note 2) (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	MPS2222 MPS2222A	f _T	250 300		MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	8.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)	MPS2222 MPS2222A	C _{ibo}	- -	30 25	pF
Input Impedance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MPS2222A MPS2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MPS2222A MPS2222A	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MPS2222A MPS2222A	h _{fe}	50 75	300 375	-
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MPS2222A MPS2222A	h _{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (I _E = 20 mAdc, V _{CB} = 20 Vdc, f = 31.8 MHz)	MPS2222A	rb′C _c	_	150	ps
Noise Figure (I _C = 100 μ Adc, V _{CE} = 10 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	MPS2222A	NF	_	4.0	dB

^{1.} Pulse Test: Pulse Width $\leq 300~\mu s$, Duty Cycle $\leq 2\%$. 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS MPS2222A only					
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc},$	t _d	-	10	ns
Rise Time	I _C = 150 mAdc, I _{B1} = 15 mAdc) (Figure 1)	t _r	-	25	ns
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc,	t _s	-	225	ns
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$ (Figure 2)	t _f	-	60	ns

SWITCHING TIME EQUIVALENT TEST CIRCUITS

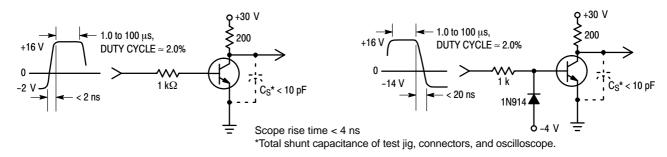


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

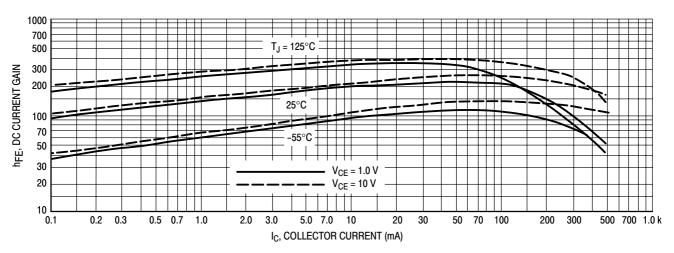


Figure 3. DC Current Gain

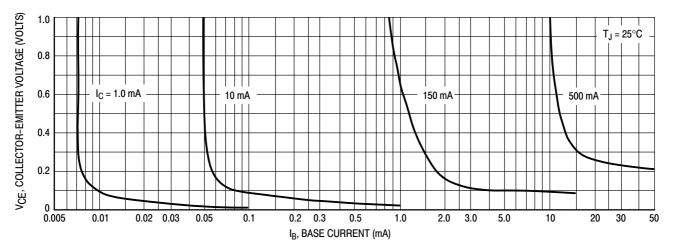


Figure 4. Collector Saturation Region

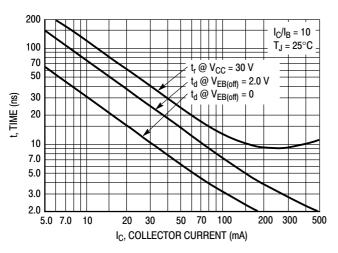


Figure 5. Turn-On Time

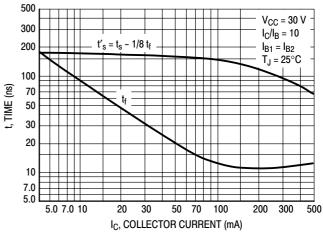


Figure 6. Turn - Off Time

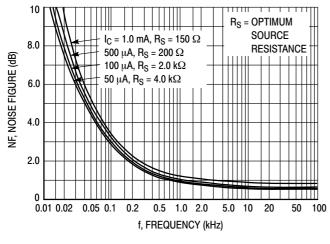


Figure 7. Frequency Effects

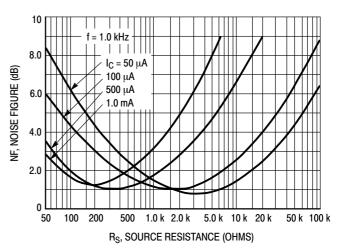
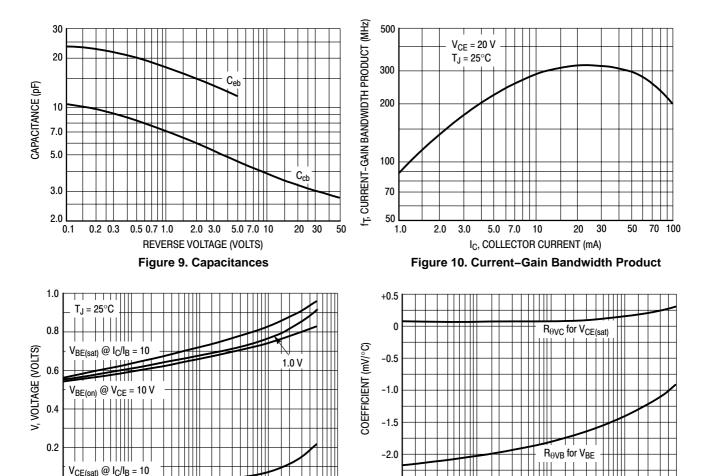


Figure 8. Source Resistance Effects



I_C, COLLECTOR CURRENT (mA)

Figure 11. "On" Voltages

5.0 10 20

50 100

200

500 1.0 k

I_C, COLLECTOR CURRENT (mA) Figure 12. Temperature Coefficients

50

100 200

5.0 10 20

ORDERING INFORMATION

0.5

0.1 0.2

1.0 2.0

Device	Package	Shipping [†]	
MPS2222G	TO-92 (Pb-Free)	5000 Units / Bulk	
MPS2222RLRP	TO-92	2000 / Tape & Ammo Box	
MPS2222RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box	
MPS2222A	TO-92	5000 Units / Bulk	
MPS2222AG	TO-92 (Pb-Free)	5000 Units / Bulk	
MPS2222ARLG	TO-92 (Pb-Free)	2000 / Tape & Reel	
MPS2222ARLRA	TO-92	2000 / Tape & Reel	
MPS2222ARLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel	
MPS2222ARLRMG	TO-92 (Pb-Free)	2000 / Tape & Reel	
MPS2222ARLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box	

-2.5

0.1 0.2

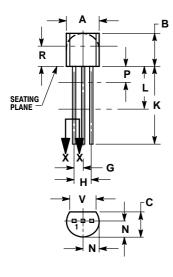
0.5

1.0 2.0

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



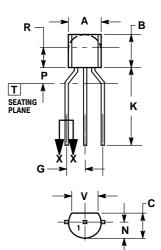
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS			
DIM	MIN MAX			
Α	4.45	5.20		
В	4.32	5.33		
С	3.18	4.19		
D	0.40	0.54		
G	2.40	2.80		
J	0.39	0.50		
K	12.70			
N	2.04	2.66		
P	1.50	4.00		
R	2.93			
V	3.43			

STYLE 1:

PIN 1 FMITTER

BASE

COLLECTOR

ON Semiconductor and una registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered readerlands of semiconductor Components industries, Ltc (SCILLC) solicit eserves the inject that changes without further holice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B